








	<h2>SI7888DP-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7888DP-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 9.4A PPAK SO-8</p> <p>Datenblätter:  SI7888DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 103701 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7888DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 30V 9.4A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	103701 pcs Stock
detaillierte Beschreibung	N-Channel 30V 9.4A (Ta) 1.8W (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	1.8W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	9.4A (Ta)
Rds On (Max) @ Id, Vgs	12 mOhm @ 12.4A, 10V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	10.5nC @ 5V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±12V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI7888DP-T1-GE3 ist neu im Original, Suche SI7888DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7888DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7888DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7892ADP-T1-E3 VISHAY SI7892ADP-T1-E3 VISHAY</p>	 <p>SI7892ADP-T1-GE3. VIS SI7892ADP-T1-GE3. VIS</p>	 <p>SI7888DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 9.4A PPAK SO-8</p>	 <p>SI7888DP SILICONIX SI7888DP SILICONIX</p>
 <p>SI7888DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 9.4A PPAK SO-8</p>	 <p>SI7888DP-T1 VISHAY VISHAY QFN</p>	 <p>SI7888DP-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 9.4A PPAK SO-8</p>	 <p>SI7892ADP-T1-GE3 V SI7892ADP-T1-GE3 V</p>

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|  SI7880ADP-T1-E3 |  SI7880ADP-T1-GE3 |  SI7880ADP-T1-GE3 |  SI7880DP-T1-GE3 |  SI7882DP-T1-E3 |
|  SI7882DP-T1-E3 |  SI7882DP-T1-GE3 |  SI7882DP-T1-GE3 |  SI7884BDP |  SI7884BDP-T1-E3 |
|  SI7884BDP-T1-E3 |  SI7884BDP-T1-GE3 |  SI7884BDP-T1-GE3 |  SI7884DP-T1-E3 |  SI7884DP-T1-GE3 |
|  SI7886ADP-T1-E3 |  SI7886ADP-T1-E3 |  SI7886ADP-T1-GE3 |  SI7886ADP-T1-GE3 |  SI7886DP |
|  SI7886DP-T1 |  SI7886DP-T1-E3 |  SI7886DP-T1-GE3 |  SI7888DP-T1-E3 |  SI7888DP-T1-E3 |
|  SI7888DP-T1-GE3 |  SI7892ADP-T1-E3 |  SI7892ADP-T1-GE3 |  SI7892ADP-T1-GE3. |  SI7892BDP-T1-E3 |
|  SI7892BDP-T1-E3 |  SI7892BDP-T1-GE3 |  SI7892BDP-T1-GE3 |  SI7892DP |  SI7892DP-T1 |
|  SI7892DP-T1-E3 |  SI7892DP-T1-GE3 |  SI7898DP |  SI7898DP-T1-E3 |  SI7898DP-T1-E3 |
|  SI7898DP-T1-GE3 |  SI7898DP-T1-GE3 |  SI7900ADN |  SI7900AEDN |  SI7900AEDN-T1 |
|  SI7900AEDN-T1-E3 |  SI7900AEDN-T1-E3 |  SI7900AEDN-T1-GE3 |  SI7900AEDN-T1-GE3 |  SI7900EDN |

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